

AMENDMENTS TO THE SPECIFICATION

Kindly amend paragraph 0071 of the application papers as indicated below:

Figure 21 is a block illustration of a W CA transistor contact 2104 illustrating preferred locations 2106 and 2108 for a localized resistor film according to the present invention. A polysilicon gate node 2112 is disposed above oxide 2116, pfet 2122 and nfet 2124 regions. By adding a resistor film 2130 between an M1 metal layer 2110 and a polysilicon gate node 2112 in a cross coupling node region 2101, at either a contact-to-M1 interface 2106 or a contact-to-polysilicon gate interface 2108, and limiting the width of the resistance film 2130 to the width of the contact via hole 2120, a localized resistor 2130 may thus be added without increasing the cell size.